

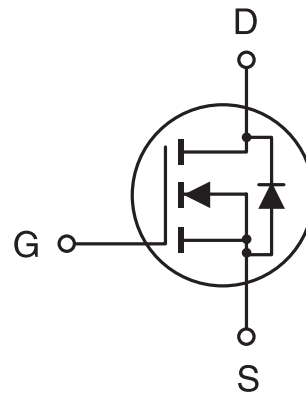
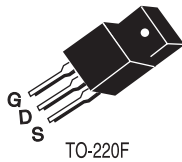
# CEFF630

PRELIMINARY

## N-Channel Enhancement Mode Field Effect Transistor

### FEATURES

- 200V , 10A ,  $R_{DS(ON)}=400m\Omega$  @  $V_{GS}=10V$
- Super high dense cell design for extremely low  $R_{DS(ON)}$ .
- High power and current handling capability.
- TO-220F full-pak for through hole.



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### ABSOLUTE MAXIMUM RATINGS (Tc=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	200	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous -Pulsed	I <sub>D</sub>	10	A
	I <sub>DM</sub>	24	A
Drain-Source Diode Forward Current	I <sub>S</sub>	5.9	A
Maximum Power Dissipation @T <sub>c</sub> =25°C Derate above 25°C	P <sub>D</sub>	35	W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R <sub>θJC</sub>	3.6	°C/W
Thermal Resistance, Junction-to-Ambient	R <sub>θJA</sub>	65	°C/W

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## ELECTRICAL CHARACTERISTICS (Tc=25°C unless otherwise noted)

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Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	200	240		V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 200V, V <sub>GS</sub> = 0V			25	μA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V			±100	nA
<b>ON CHARACTERISTICS<sup>a</sup></b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA	2		4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10V, I <sub>D</sub> = 3.5A		270	400	mΩ
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>GS</sub> = 10V, V <sub>DS</sub> = 10V	10			A
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 3.5A	3			S
<b>DYNAMIC CHARACTERISTICS<sup>b</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V f = 1.0MHz		650	800	pF
Output Capacitance	C <sub>OSS</sub>			110	250	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			45	55	pF
<b>SWITCHING CHARACTERISTICS<sup>b</sup></b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 100V, I <sub>D</sub> = 5A, V <sub>GS</sub> = 10V, R <sub>GEN</sub> = 50Ω			60	ns
Rise Time	t <sub>r</sub>				120	ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>				80	ns
Fall time	t <sub>f</sub>				50	ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 160V, I <sub>D</sub> = 5.9A, V <sub>GS</sub> = 10V		24	60	nC
Gate-Source Charge	Q <sub>gs</sub>			6		nC
Gate-Drain Charge	Q <sub>gd</sub>			7		nC

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## ELECTRICAL CHARACTERISTICS (T<sub>c</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>DRAIN-SOURCE DIODE CHARACTERISTICS <sup>a</sup></b>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 5.9A			1.5	V

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### Notes

- a. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

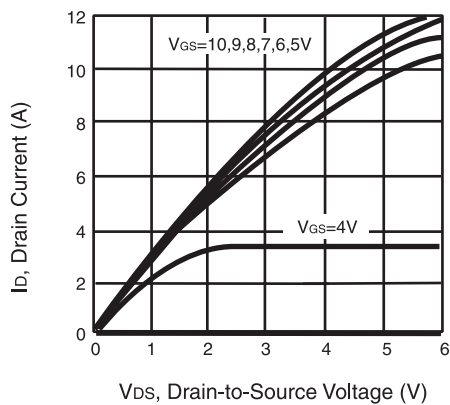


Figure 1. Output Characteristics

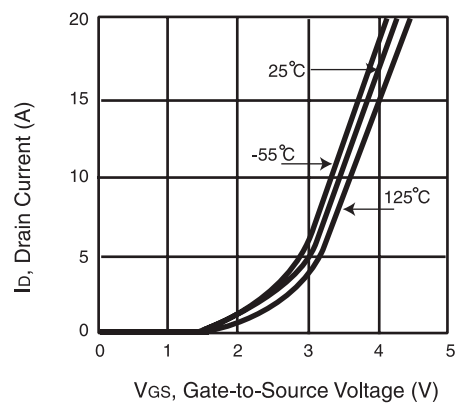


Figure 2. Transfer Characteristics

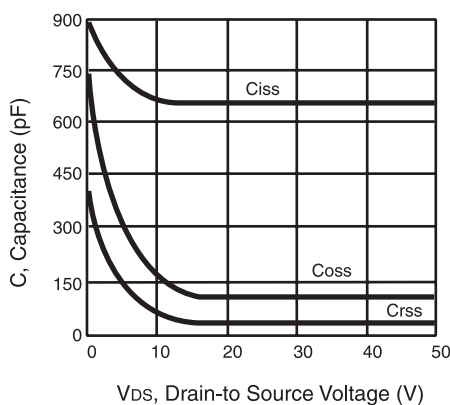


Figure 3. Capacitance

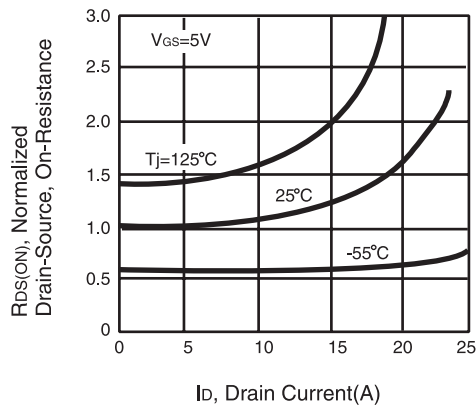
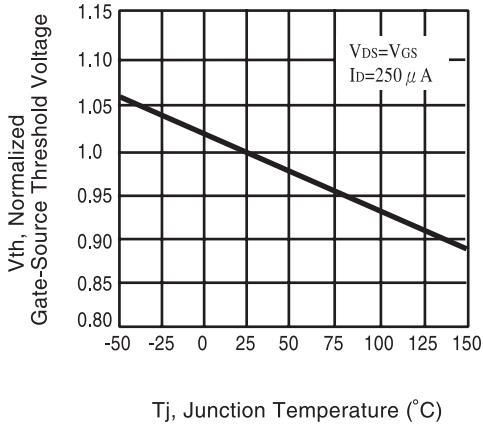


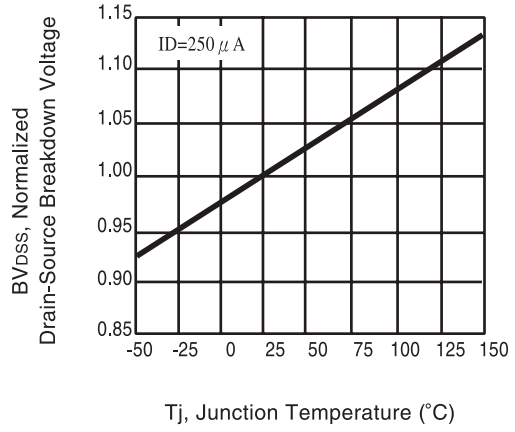
Figure 4. On-Resistance Variation with Drain Current and Temperature

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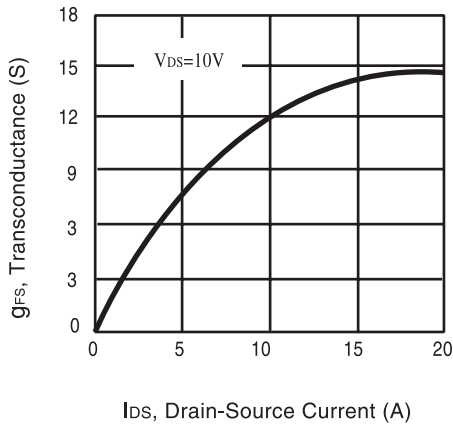
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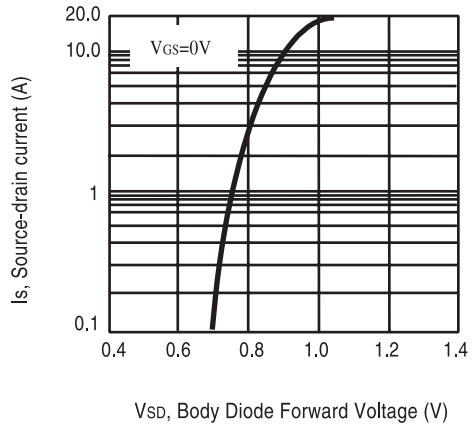
**Figure 5. Gate Threshold Variation with Temperature**



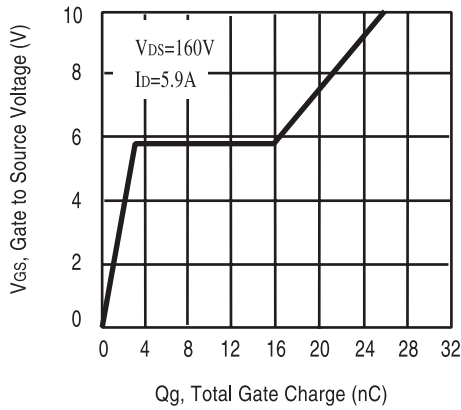
**Figure 6. Breakdown Voltage Variation with Temperature**



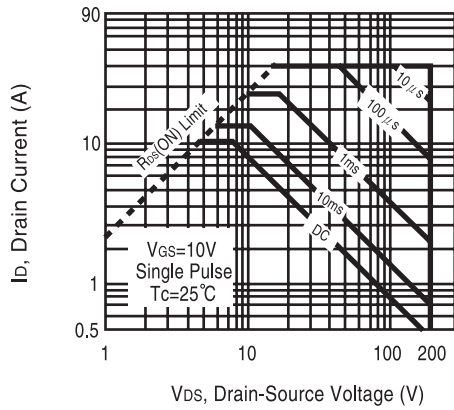
**Figure 7. Transconductance Variation with Drain Current**



**Figure 8. Body Diode Forward Voltage Variation with Source Current**



**Figure 9. Gate Charge**



**Figure 10. Maximum Safe Operating Area**

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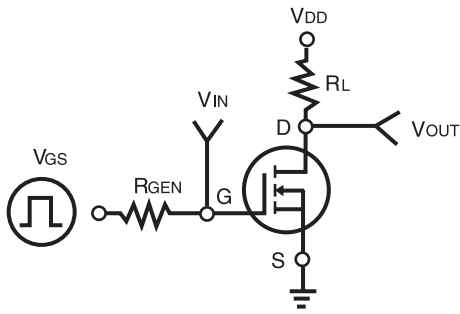


Figure 11. Switching Test Circuit

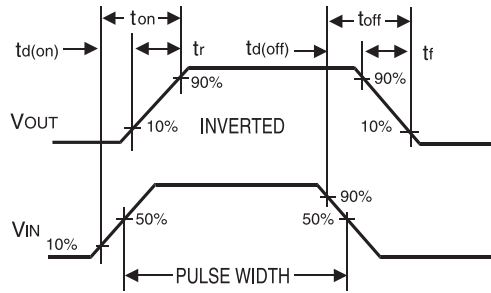


Figure 12. Switching Waveforms

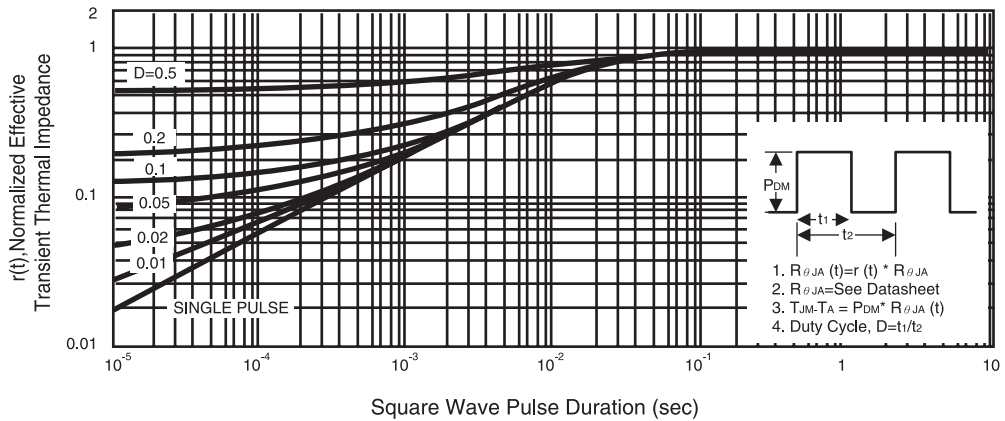


Figure 13. Normalized Thermal Transient Impedance Curve